FAIRCHILD SEMICONDUCTOR®

August 2005

FGA25N120ANTD
1200V NPT Trench IGBT

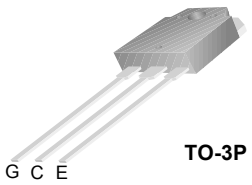
Features

- NPT Trench Technology, Positive temperature coefficient
- Low saturation voltage: $V_{CE(sat),\ typ}$ = 2.0V @ I_C = 25A and T_C = 25°C
- Low switching loss: $E_{off,\ typ}$ = 0.96mJ @ I_C = 25A and T_C = 25°C
- Extremely enhanced avalanche capability

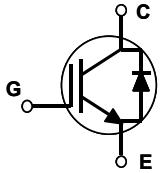
Description

Using Fairchild's proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation.

This device is well suited for the resonant or soft switching application such as induction heating, microwave oven, etc.



TO-3P



Absolute Maximum Ratings

Symbol	Description		FGA25N120ANTD	Units
V_{CES}	Collector-Emitter Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	50	A
	Collector Current	@ T_C = 100°C	25	A
I_{CM}	Pulsed Collector Current (Note 1)		75	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	25	A
I_{FM}	Diode Maximum Forward Current		150	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	312	W
	Maximum Power Dissipation	@ T_C = 100°C	125	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8” from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for IGBT	--	0.4	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for Diode	--	2.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGA25N120ANTD	FGA25N120ANTD	TO-3P	--	--	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0V	--	--	3	mA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0V	--	--	± 250	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 25mA, V_{CE} = V_{GE}	3.5	5.5	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 25A, V_{GE} = 15V	--	2.0	2.5	V
		I_C = 25A, V_{GE} = 15V, T_C = 125°C	--	2.15	--	V
		I_C = 50A, V_{GE} = 15V	--	2.65	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	--	3700	--	pF
C_{oes}	Output Capacitance		--	130	--	pF
C_{res}	Reverse Transfer Capacitance		--	80	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 25A, R_G = 10Ω, V_{GE} = 15V, Inductive Load, T_C = 25°C	--	50	--	ns
t_r	Rise Time		--	60	90	ns
$t_{d(off)}$	Turn-Off Delay Time		--	190	--	ns
t_f	Fall Time		--	100	180	ns
E_{on}	Turn-On Switching Loss		--	4.1	6.2	mJ
E_{off}	Turn-Off Switching Loss		--	0.96	1.5	mJ
E_{ts}	Total Switching Loss		--	5.06	7.7	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 25A, R_G = 10Ω, V_{GE} = 15V, Inductive Load, T_C = 125°C	--	50	--	ns
t_r	Rise Time		--	60	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	200	--	ns
t_f	Fall Time		--	154	--	ns
E_{on}	Turn-On Switching Loss		--	4.3	6.9	mJ
E_{off}	Turn-Off Switching Loss		--	1.5	2.4	mJ
E_{ts}	Total Switching Loss		--	5.8	9.3	mJ
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 25A, V_{GE} = 15V	--	200	300	nC
Q_{ge}	Gate-Emitter Charge		--	15	23	nC
Q_{gc}	Gate-Collector Charge		--	100	150	nC

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	I_F = 25A	T_C = 25°C	--	2.0	3.0	V
			T_C = 125°C	--	2.1	--	
t_{rr}	Diode Reverse Recovery Time	I_F = 25A dI/dt = 200 A/μs	T_C = 25°C	--	235	350	ns
			T_C = 125°C	--	300	--	
I_{rr}	Diode Peak Reverse Recovery Current		T_C = 25°C	--	27	40	A
			T_C = 125°C	--	31	--	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	--	3130	4700	nC
			T_C = 125°C	--	4650	--	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

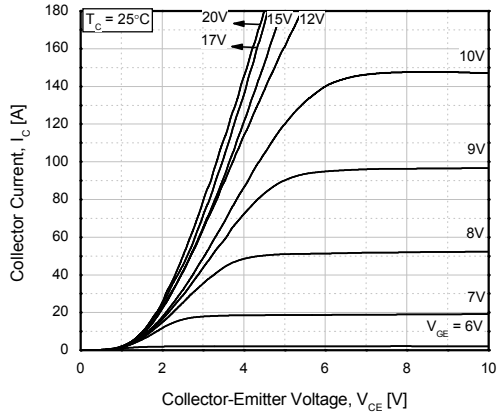


Figure 2. Typical Saturation Voltage Characteristics

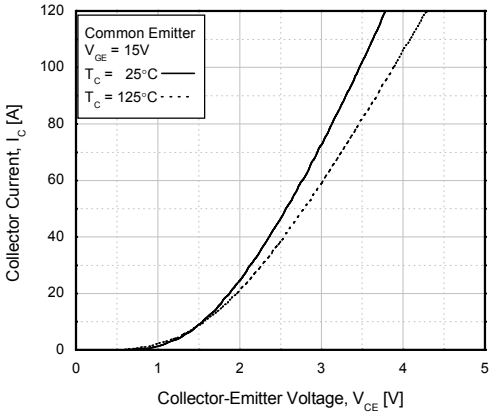


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

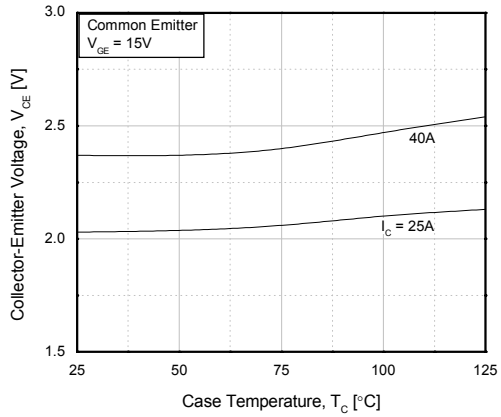


Figure 4. Saturation Voltage vs. V_{GE}

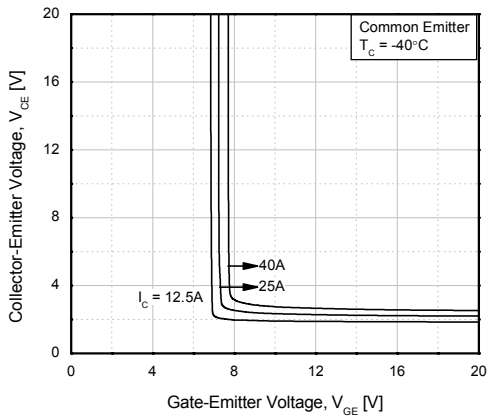


Figure 5. Saturation Voltage vs. V_{GE}

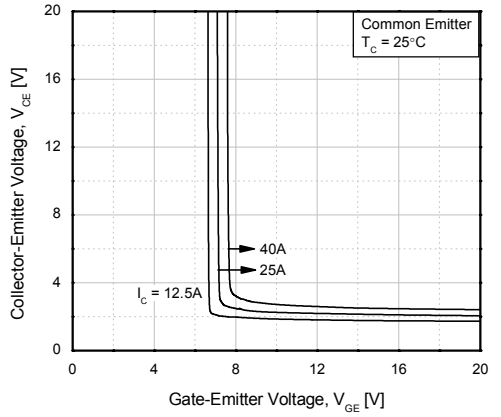
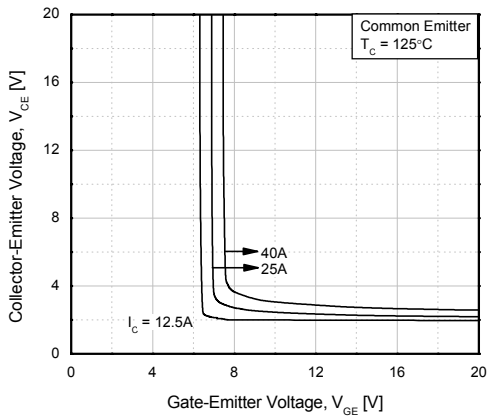


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

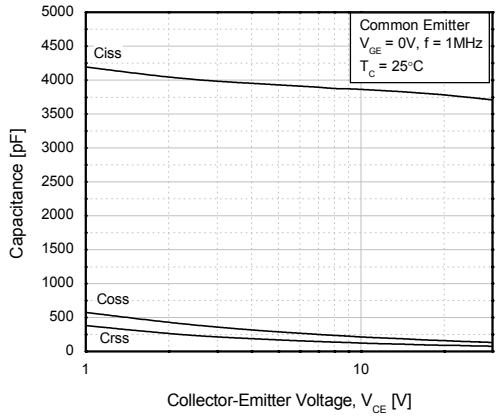


Figure 8. Turn-On Characteristics vs. Gate Resistance

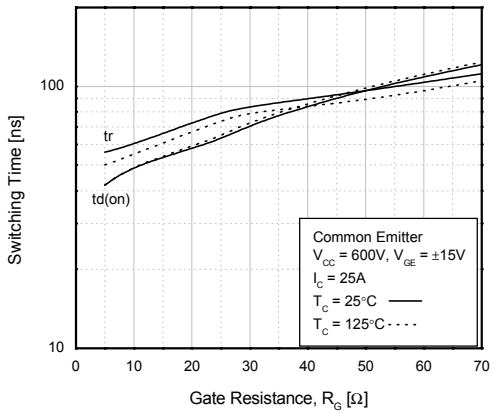


Figure 9. Turn-Off Characteristics vs. Gate Resistance

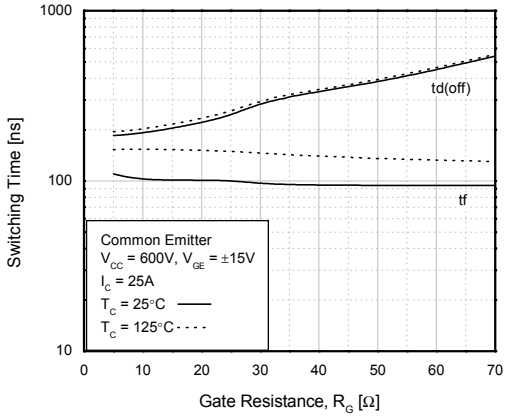


Figure 10. Switching Loss vs. Gate Resistance

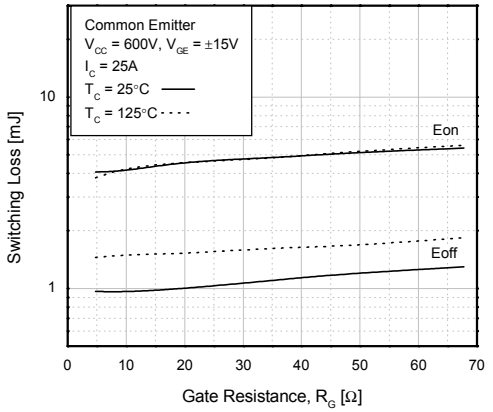


Figure 11. Turn-On Characteristics vs. Collector Current

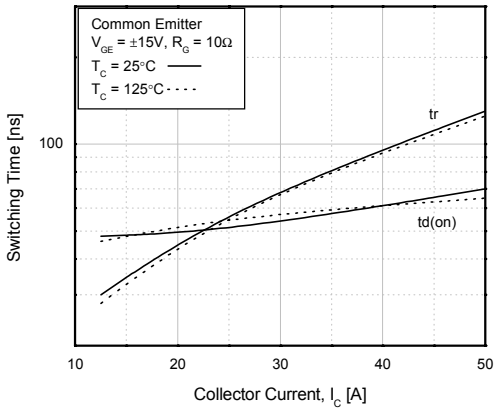
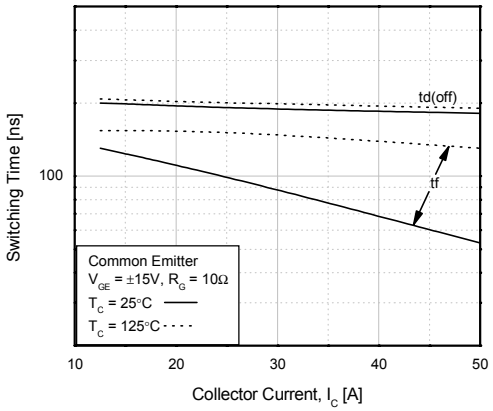


Figure 12. Turn-Off Characteristics vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

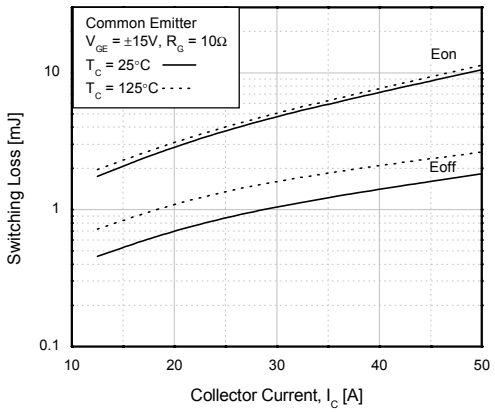


Figure 14. Gate Charge Characteristics

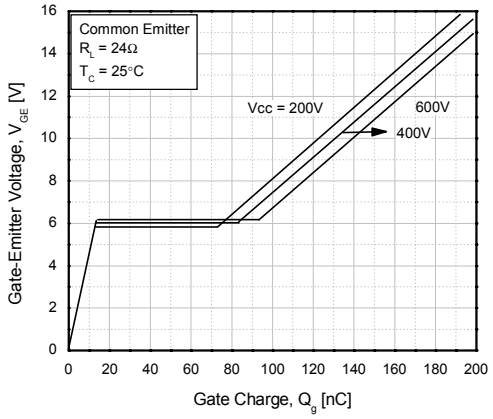


Figure 15. SOA Characteristics

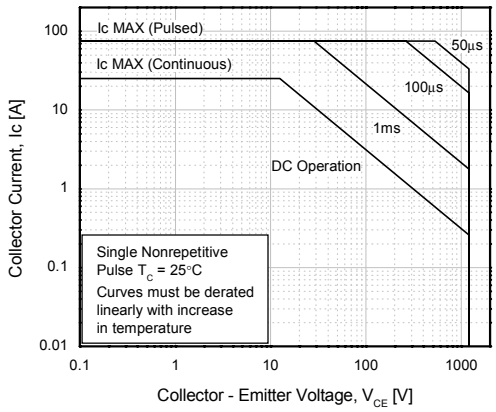


Figure 16. Turn-Off SOA

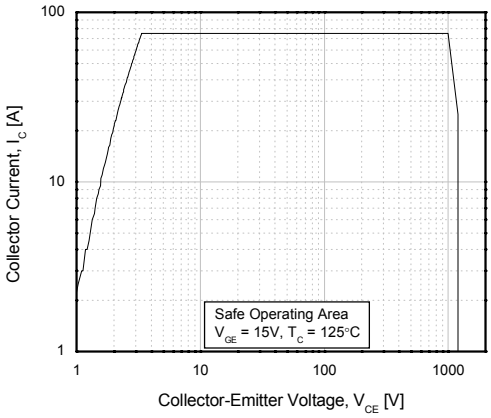
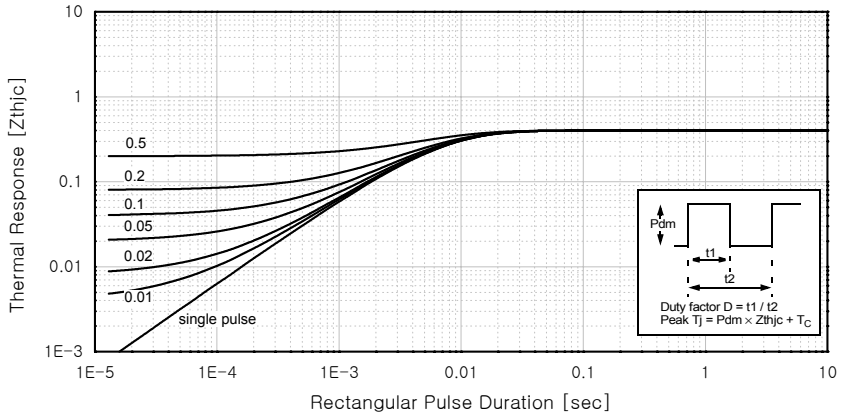


Figure 17. Transient Thermal Impedance of IGBT



Typical Performance Characteristics (Continued)

Figure 18. Forward Characteristics

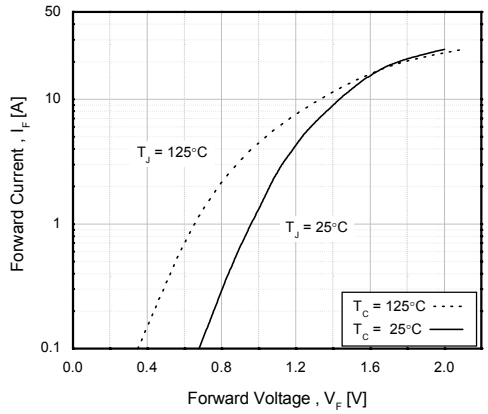


Figure 19. Reverse Recovery Current

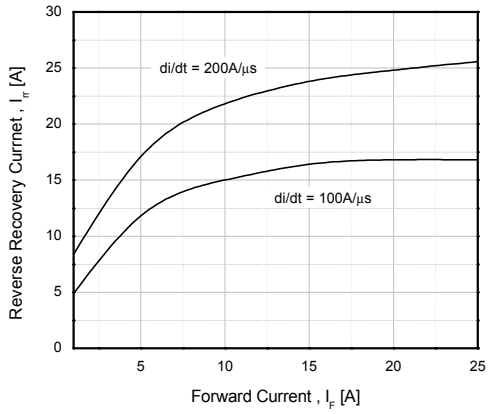


Figure 20. Stored Charge

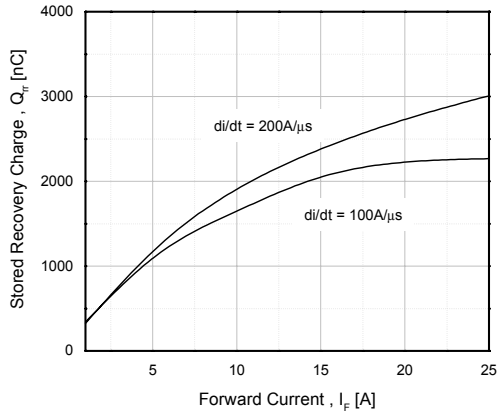
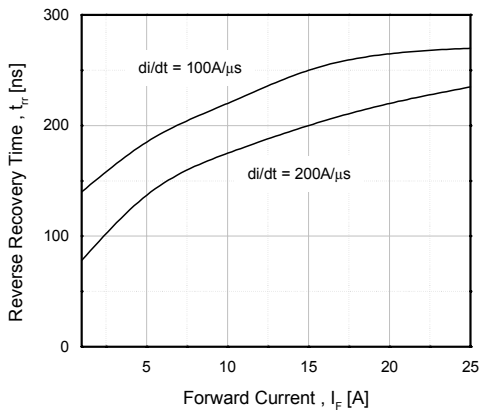
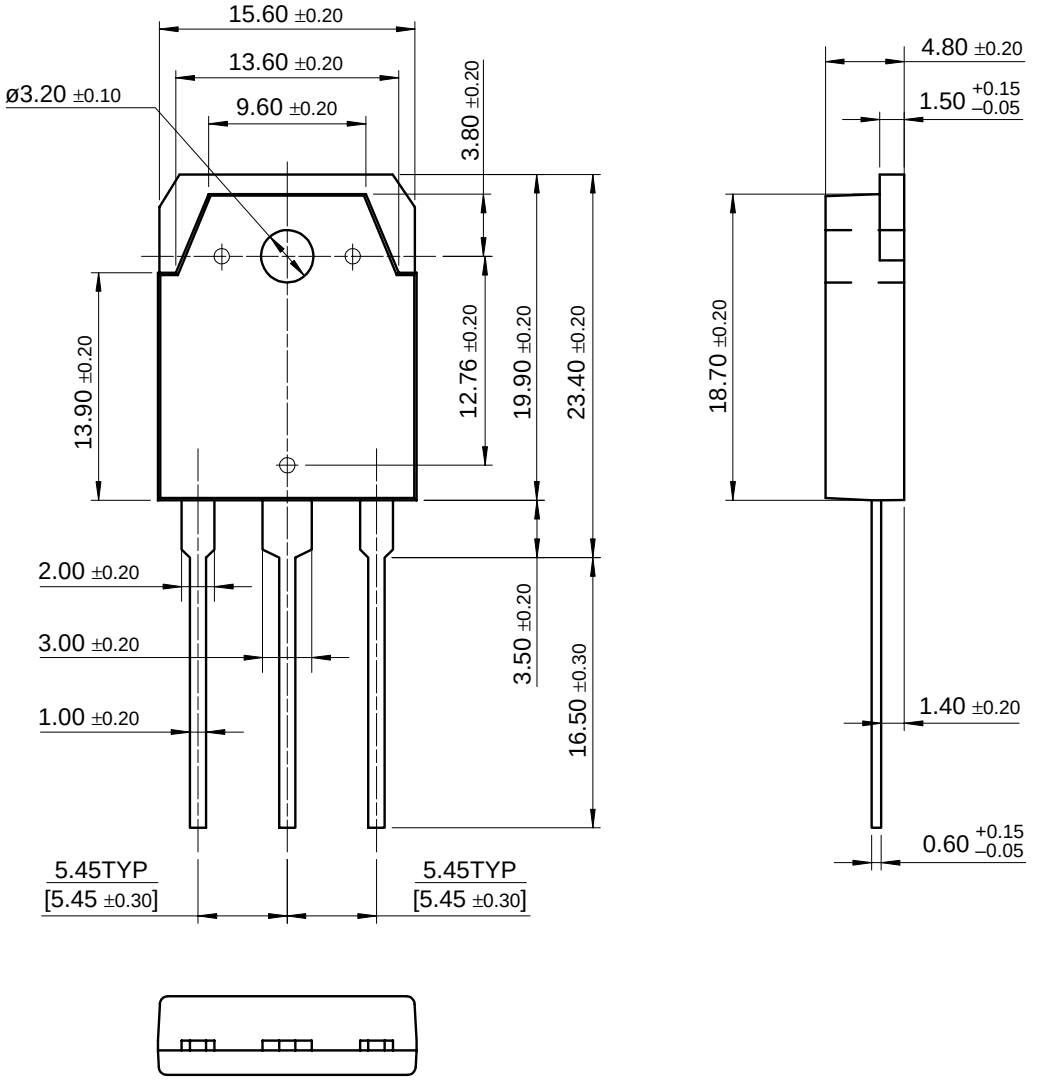


Figure 21. Reverse Recovery Time



Mechanical Dimensions

TO-3P



Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™
ActiveArray™
Bottomless™
Build it Now™
CoolFET™
CROSSVOLT™
DOME™
EcoSPARK™
E^2CMOS™
EnSigna™
FACT™
FACT Quiet Series™
FAST®
FASTr™
FPS™
FRFET™
GlobalOptoisolator™
GTO™
HiSeC™
I^2C™
i-Lo™
ImpliedDisconnect™
IntelliMAX™
ISOPLANAR™
LittleFET™
MICROCOUPLER™
MicroFET™
MicroPak™
MICROWIRE™
MSX™
MSXPro™
OCX™
OCXPro™
OPTOLOGIC®
OPTOPLANAR™
PACMAN™
POP™
Power247™
PowerEdge™
PowerSaver™
PowerTrench®
QFET®
QS™
QT Optoelectronics™
Quiet Series™
RapidConfigure™
RapidConnect™
µSerDes™
SILENT SWITCHER®
SMART START™
SPM™
Stealth™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SyncFET™
TinyLogic®
TINYOPTO™
TruTranslation™
UHC™
UltraFET®
UniFET™
VCX™
Wire™

Across the board. Around the world.™
The Power Franchise®
Programmable Active Droop™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. I16